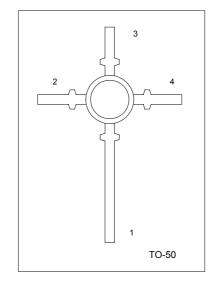
UTC 2SC3358 NPN SILICON EPITAXIALTRANSISTOR

HIGH FREQUENCY LOW NOISE **AMPLIFIER**

FEATURES

- *Low Noise and High Gain
- *High Power Gain



1:COLLECTOR 2:EMITTER 3:BASE 4:EMITTER

ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	Vсво	20	V
Collector-emitter voltage	VCEO	12	V
Emitter-base voltage	VEBO	3	V
Collector current	lc	100	mA
Total power dissipation	Рт	250	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I _{CBO}	V_{CB} =10V, I_{E} =0			1.0	μΑ
Emitter Cutoff Current	I _{EBO}	$V_{EB}=1V$, $I_{C}=0$			1.0	μА
DC Current Gain	h _{FE}	V_{CE} =10V, I_{C} =20mA	50		300	
Gain bandwidth Product	fT	V_{CE} =10V, I_{C} =20mA		7		GHz
Feed-Back Capacitance	Cre	V_{CB} =10V, I_E =0, f=1.0MHz			1.0	pF
Noise figure	NF	V _{CE} =10V, I _C =7mA, f=1.0GHz			2.0	dB

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QW-R212-001,A

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